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Semiconductor devices –
Part 5-16: Optoelectronic devices – Light emitting diodes – Test method of the flat-band voltage of GaN-based light emitting diodes based on the photocurrent spectroscopy

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Draft	Report on voting
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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

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SEMICONDUCTOR DEVICES –

Part 5-16: Optoelectronic devices – Light emitting diodes – Test method of the flat-band voltage of GaN-based light emitting diodes based on the photocurrent spectroscopy

1 Scope

This part of IEC 60747 specifies the measuring method of flat-band voltage of single GaN-based light emitting diode (LED) die or package without phosphor, based on the photocurrent (PC) spectroscopy. White LEDs for lighting applications are out of the scope of this part of IEC 60747.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60747-5-6:2021, *Semiconductor devices – Part 5-6: Optoelectronic devices – Light emitting diodes*

IEC 60747-5-15:2022, *Semiconductor devices – Part 5-15: Optoelectronic devices – Light emitting diodes – Test method of the flat-band voltage based on the electroreflectance spectroscopy*